

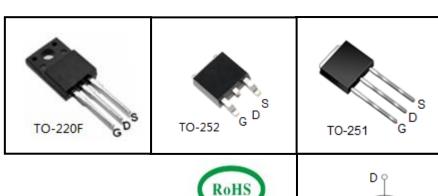
# **60V N-Channel MOSFET**

### **FEATURES**

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

#### **APPLICATIONS**

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)





Device Marking and Package Information				
Device	Package	Marking		
TMA50N06H	TO-220F	A50N06H		
TMD50N06H	TO-252	D50N06H		
TMU50N06H	TO-251	U50N06H		

<b>Absolute Maximum Ratings</b> $T_C = 25^{\circ}C$ , unless otherwise noted						
Boromotor	0	Completel		Value		
Parameter		Symbol	TO-220F	TO-251	TO-252	Unit
Drain-Source Voltage (V <sub>GS</sub> = 0V)		V <sub>DSS</sub>		60		V
Continuous Drain Current		I <sub>D</sub>	50			А
Pulsed Drain Current (note	e1)	I <sub>DM</sub>	200		А	
Gate-Source Voltage		$V_{GSS}$	±20			V
Single Pulse Avalanche Energy (note	2)	E <sub>AS</sub>	280		mJ	
Avalanche Current (note	e1)	I <sub>AR</sub>	50		А	
Repetitive Avalanche Energy (note	e1)	E <sub>AR</sub>	36		mJ	
Power Dissipation (T <sub>C</sub> = 25°C)		$P_{D}$	83	1	10	W
Operating Junction and Storage Temperature Range		$T_J$ , $T_{stg}$	-55~+150		°C	

Thermal Resistance					
Barrana	O. mala al	Value			
Parameter	Symbol	TO-220F	TO-251	TO-252	Unit
Thermal Resistance, Junction-to-Case	R <sub>thJC</sub>	1.5	1.14		00.00
Thermal Resistance, Junction-to-Ambient	R <sub>thJA</sub>	62.5	6	0	•C/W

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Specifications T <sub>J</sub> = 25°C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value Min. Typ. Max			Unit
Static				Тур.	Max.	
	.,,	V 0V I 050 A		T		.,
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0V, I_{D} = 250\mu A$	60			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 60V, V_{GS} = 0V, T_{J} = 25^{\circ}C$			5	μA
		$V_{DS} = 48V, V_{GS} = 0V, T_{J} = 125^{\circ}C$			100	
Gate-Source Leakage	I <sub>GSS</sub>	$V_{GS} = \pm 20V$			±100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.0		4.0	٧
Drain-Source On-Resistance (Note3)	R <sub>DS(on)</sub>	$V_{GS} = 10V, I_D = 25A$		14	22	mΩ
Dynamic					-	
Input Capacitance	C <sub>iss</sub>	V 0V		1489		pF
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0V$ , $V_{DS} = 25V$ ,		608		
Reverse Transfer Capacitance	C <sub>rss</sub>	f = 1.0MHz		275		
Total Gate Charge	$Q_g$			60		nC
Gate-Source Charge	$Q_{gs}$	$V_{DD} = 48V, I_{D} = 50A,$ $V_{GS} = 10V$		6		
Gate-Drain Charge	$Q_{gd}$			31		
Turn-on Delay Time	t <sub>d(on)</sub>			22		
Turn-on Rise Time	t <sub>r</sub>	$V_{DD} = 30V, I_{D} = 50A,$		82		- ns
Turn-off Delay Time	t <sub>d(off)</sub>	$R_G = 25 \Omega$		52		
Turn-off Fall Time	t <sub>f</sub>			93		
Drain-Source Body Diode Character	istics		•	•		
Continuous Body Diode Current	I <sub>S</sub>				50	
Pulsed Diode Forward Current	I <sub>SM</sub>	T <sub>C</sub> = 25 °C			200	А
Body Diode Voltage	V <sub>SD</sub>	$T_J = 25^{\circ}C$ , $I_{SD} = 50A$ , $V_{GS} = 0V$			2	V
Reverse Recovery Time	t <sub>rr</sub>	$V_{GS} = 0V, I_{S} = 50A,$		68		ns
Reverse Recovery Charge	Q <sub>rr</sub>	di <sub>F</sub> /dt =100A /µs		4.2		μC

#### Notes

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature
- 2.  $I_{AS}$  = 50A,  $V_{DD}$  = 50V,  $R_{G}$  = 25  $\Omega$ , Starting  $T_{J}$  = 25  $^{\circ}C$
- 3. Pulse Test: Pulse width ≤ 300µs, Duty Cycle ≤ 1%



## **Typical Characteristics** $T_J = 25^{\circ}\text{C}$ , unless otherwise noted

Figure 1. Output Characteristics (T<sub>J</sub> = 25°C)

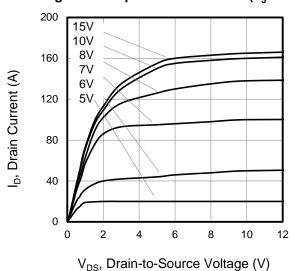


Figure 3. Drain Current vs. Temperature

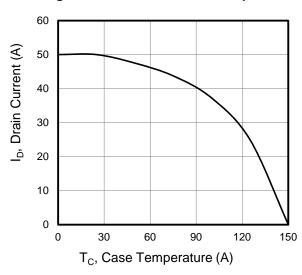


Figure 5. Transfer Characteristics

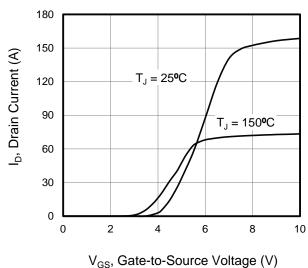


Figure 2. Body Diode Forward Voltage

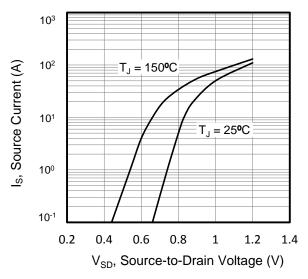
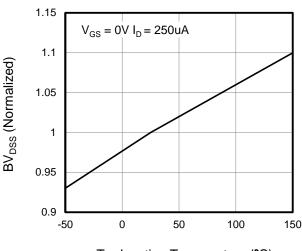
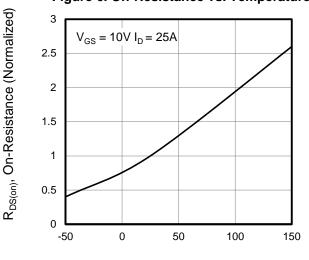


Figure 4. BV<sub>DSS</sub> Variation vs. Temperature



T<sub>J</sub>, Junction Temperature (°C)

Figure 6. On-Resistance vs. Temperature



T<sub>.J</sub>, Junction Temperature (°C)



## **Typical Characteristics** $T_J = 25^{\circ}C$ , unless otherwise noted

V<sub>GS</sub>, Gate-to-Source Voltage (V)

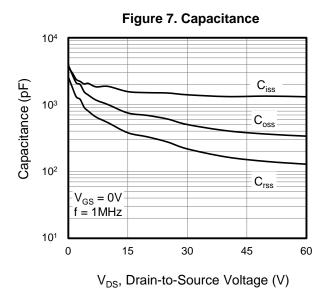


Figure 9. Transient Thermal Impedance TO-220F

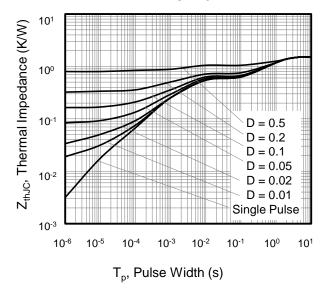
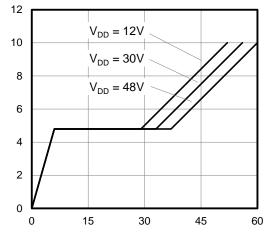


Figure 8. Gate Charge



Q<sub>g</sub>, Total Gate Charge (nC)

Figure 10. Transient Thermal Impedance TO-251,TO-252

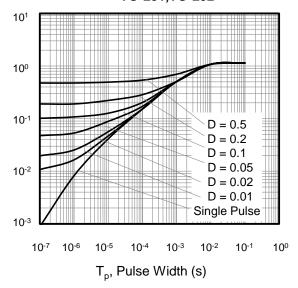




Figure A: Gate Charge Test Circuit and Waveform

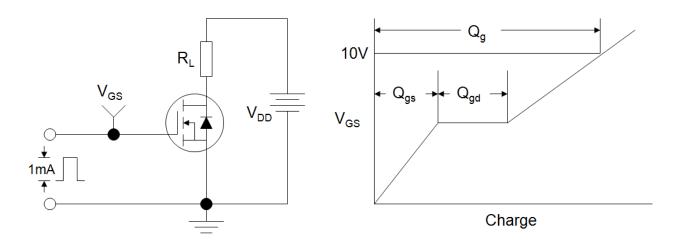


Figure B: Resistive Switching Test Circuit and Waveform

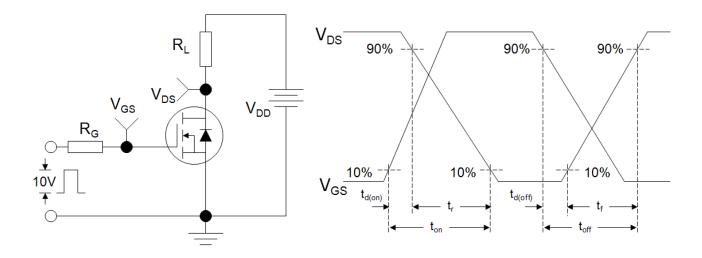
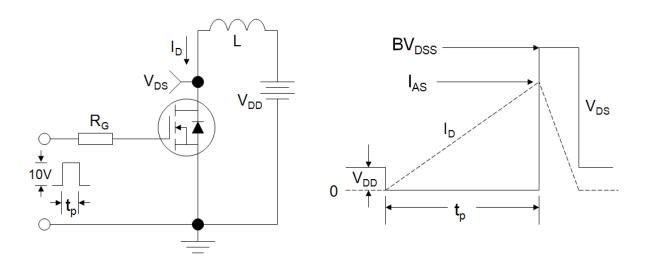
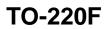


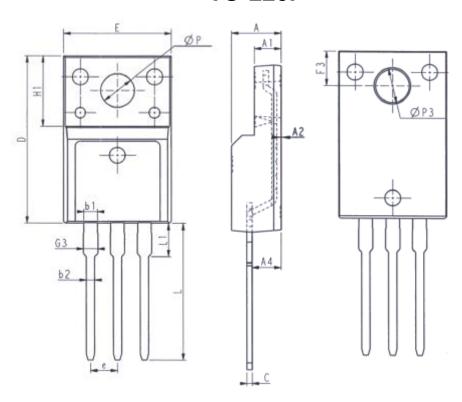
Figure C: Unclamped Inductive Switching Test Circuit and Waveform



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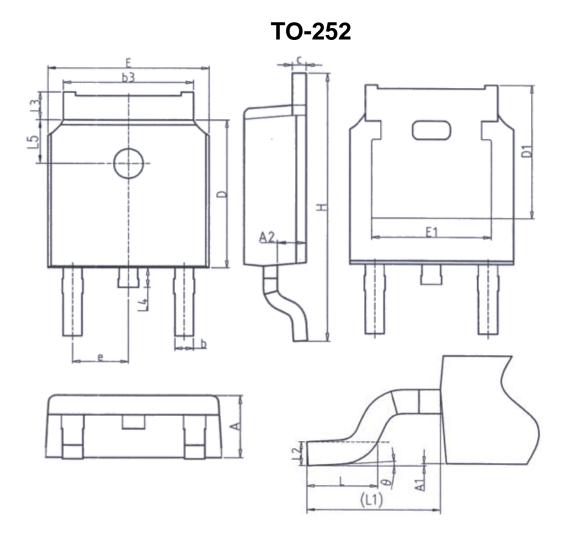




Unit: mm			Unit: mm			
Symbol	Min.	Max.	Symbol	Min.	Max.	
E	9. 96	10. 36	L	12. 68	13. 28	
Α	4. 50	4. 90	L1	2. 93	3. 13	
<b>A</b> 1	2. 34	2. 74	Р	3. 03	3. 38	
A2	0. 30	0. 60	Р3	3. 15	3. 65	
A4	2. 56	2. 96	F3	3. 15	3. 45	
С	0. 40	0. 65	G3	1. 25	1. 55	
D	15. 57	16. 17	b1	1. 18	1. 43	
H1	6. 70REF		b2	0. 70	0. 95	
e	2. 54BSC					

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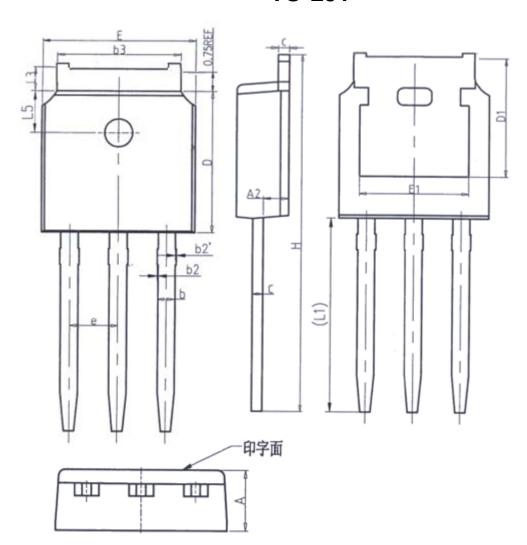


Unit: mm				
Symbol	Min.	Max.		
Α	2. 20	2. 40		
A1	0.00	0. 20		
A2	0. 97	1. 17		
b	0. 68	0. 90		
b3	5. 20	5. 50		
С	0. 43	0. 63		
D	5. 98	6. 22		
D1	D1 5. 30REF			
E	6. 40	6. 80		
E1	_			

Unit: mm				
Symbol	Min.	Max.		
е	2. 28	6BSC		
Н	9. 40	10.50		
L	1. 38	1. 75		
L1	2. 90REF			
L2	0. 51	IBSC		
L3	0.88	1. 28		
L4	_	1.00		
L5	1. 65	1. 95		
θ	0°	8°		



# TO-251



Unit: mm				
Symbol	Min.	Max.		
Α	2. 20	2. 40		
A2	0. 97	1. 17		
b	0. 68	0. 90		
b2	0.00	0.10		
b2′	0.00	0.10		
b3	5. 20	5. 50		
С	0. 43	0. 63		
D	5. 98	6. 22		

Unit: mm			
Symbol	Min.	Max.	
D1	5. 30REF		
E	6. 40	6. 80	
E1	4. 63	-	
е	2. 286BSC		
Н	16. 22	16. 82	
L1	9. 15	9. 65	
L3	0. 88	1. 28	
L5	1. 65	1. 95	



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